

ABSTRACT

The present invention relates to a thin film transistor for preventing short of circuit by step and a method for fabricating the thin film transistor and provides a thin film transistor including a buffer layer formed on glass substrate; an activation layer formed on the buffer layer; and a gate insulation layer formed on the buffer layer including the activation layer, with the buffer layer having a step formed between a lower part of the activation layer and a part except the lower part of the activation layer.